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APPLICATION NO.	FILING DATE	TVD 07334	<u></u>	
		FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/643,877	08/20/2003	Mu-Yi · Liu	COR 131	5190
75	05/11/2004		EXAM	NED
RABIN & BERDO, PC Suite 500			PRENTY, MARK V	
1101 14th Street Washington, Do	, N.W.		ART UNIT	PAPER NUMBER
washington, Do	20005		2822	
	• •		DATE MAILED: 05/11/2004	e e e e e e e e e e e e e e e e e e e

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)
Office A die	10/643,877	LIU ET AL.
Office Action Summary	Examin r	Art Unit
The state of the s	MARK V PRENTY	1
Th MAILING DATE of this communication app Period for Reply	ars on the cover she t with the co	correspond nce address
A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply if NO period for reply is specified above, the maximum statutory period with the period for reply within the set or extended period for reply will, by statute, any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	IS SET TO EXPIRE 3 MONTH(6(a). In no event, however, may a reply be time within the statutory minimum of thirty (30) days ill apply and will expire SIX (6) MONTHS from	S) FROM ely filed will be considered timely.
Status		
1) Responsive to communication(s) filed on 20 Au 2a) This action is FINAL. 2b) This a 3) Since this application is in condition for allowand closed in accordance with the practice under Ex	action is non-final.	secution as to the merits is
Disposition of Claims	parte Quayle, 1935 C.D. 11, 453	3 O.G. 213.
4) ☐ Claim(s) 1-3 is/are pending in the application. 4a) Of the above claim(s) is/are withdrawr 5) ☐ Claim(s) is/are allowed. 6) ☐ Claim(s) 1 and 3 is/are rejected. 7) ☐ Claim(s) 2 is/are objected to. 8) ☐ Claim(s) are subject to restriction and/or expressions.		
Application Papers 9)☐ The specification is objected to by the Examiner.		
10) The drawing(s) filed on 20 August 2003 is/are: a) Applicant may not request that any objection to the	Maccontod or h) about	
The draw of the dr	Wing(s) he hold in an array	
Including the correction	in room in a difficult	•
11) The oath or declaration is objected to by the Exam	niner. Note the attached Office A	tion or form DTO 450
Priority under 35 U.S.C. § 119		
12) Acknowledgment is made of a claim for foreign price a) All b) Some * c) None of: 1. Certified copies of the priority documents ha) or (f).
Certified copies of the priority documents ha	We been recoived in Ameliana	
or the certified copies of the priority of	documents have been received:	NO
The state of the s	L. L. RUIG 17:2/6\\	r triis National Stage
* See the attached detailed Office action for a list of the	ne certified copies not received	
Attachment(s)		3. 1 · 1 · 1 · 1 · 1 · 1 · 1 · 1 · 1 · 1
1) Notice of References Cited (PTO-892)	. —	
2) 🖾 Notice of Draftsperson's Patent Drawing Povious (BTO 040)	4) Interview Summary (PTC Paper No(s)/Mail Date	D-413)
Paper No(s)/Mail Date	5) Notice of Informal Patent 6) Other:	Application (PTO-152)
U.S. Patent and Trademark Office PTOL-326 (Rev. 1-04) Office Action 5		

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This Office Action is in response to the papers filed on August 20, 2003.

Claims 1 and 3 are rejected under 35 U.S.C. 102(e) as being anticipated by Yoshino (United States Patent Application Publication US 2003/0160280).

With respect to independent claim 1, Yoshino discloses (see the entire reference, including the Figs. 11-13 disclosure) an ONO flash memory array for improving a disturbance between adjacent memory cells, comprising: a substrate 1 having first and second buried diffusion regions 2 and 3; a channel between the first and second buried diffusion regions; an ONO layer 4/5/6 above the channel for memory storage; a first pocket 15 of a first concentration implanted on one side of the channel close to the first buried diffusion region; and a second pocket 16 of a second concentration implanted on the other side of the channel close to the second buried diffusion region.

Claim 1 is thus rejected under 35 U.S.C. 102(e) as being anticipated by Yoshino.

With respect to independent claim 3, Yoshino discloses (see the entire reference, including the Figs. 11-13 disclosure) an ONO flash memory array for improving a disturbance between adjacent memory cells, comprising: a substrate 1 having first and second buried diffusion regions 2 and 3; a channel between the first and second buried diffusion regions; an ONO layer 4/5/6 above the channel for memory storage; and a pocket 15 implanted on one side of the channel close to the first buried diffusion region.

Claim 3 is thus rejected under 35 U.S.C. 102(e) as being anticipated by Yoshino.

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Claim 2 is objected to as being dependent upon a rejected base claim, but would be allowable over the prior art of record if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

The prior art of record does not disclose or suggest the claimed ONO flash memory array taken as a whole, including the first and second pockets.

Registered practitioners can telephone the examiner at (571) 272-1843. Any voicemail message left for the examiner must include the name and registration number of the registered practitioner calling, and the Application/Control (Serial) Number. Technology Center 2800's general telephone number is (571) 272-2800.

Mark V. Prenty Primary Examiner

Mark Pren